Memory systems



Memory technology

- DRAM Dynamic Random Access Memory
 - bits are represented by an electric charge in a small capacitor
 - charge leaks away, need to be refreshed at regular intervals
 - reading the memory also discarges the capacitors
- DRAM has better price/performance than SRAM
 - also higher densities, need less power and dissipate less heat
- SRAM Static Random Access Memory
 - based on gates, a bit is stored in 4–6 transistors
 - no refreshing, retain data as long as they have power
- SRAM provides higher speed
 - used for high-performance memories
 - cache, video memory, ...

Access time and cycle time

- Memory access time is the time it takes read or write a memory location
- Memory cycle time is the minimum time between two successive memory references
 - can not do repeated accesses immediately after each other
 - have to refresh the memory after an access

Example:

- 50 ns access time
- 100 ns cycle time

Memory banks and interleaving

- The memory is organized as a number of banks
 - each bank consists of a separate memory device
- Interleaving
 - consecutive memory accesses address different banks
 - · when one bank is refreshed, another bank can be accesed
 - can overlap accesses and refreshing
- Gives a continous flow of data from memory
- Example:
 - 2-way interleaved memory



4

Dynamic RAM technology

Fast page mode DRAM

- improves access to memory in sequentially located addresses (cache lines)
- the entire address does not have to be transmitted to the memory for each access, only the least significant bits
- EDO RAM (Extended Data OUT RAM)
 - very similar to fast page mode RAM
- SDRAM (Synchronous DRAM)
 - CPU and memory is synchronized by an external clock
 - consecutive data is output synchronously on a clock pulse
 - memory chips are divided into two independent cell banks, interleaving
 - PC66, PC100, PC133 SDRAM, etc.
 - 133 MHz * 64 bits / 8 bits = 1064 MB/s peak bandwidth
 - typical efficiency approx. 75 % = 800 MB/s

5

6

Dynamic RAM technology (cont.)

DDR SDRAM (Double Data Rate SDRAM)

- memory architecture chosen by AMD
- synchronous DRAM
- the memory chips perform accesses on both the rising and falling edges of the clock
- a memory with a 133 MHz clock operates effectively at 266 MHz
- 64-bit data bus
- 133 MHz clock cycle * 2 clocks/cycle * 64 bits / 8 bits = 2128 MB/s peak bandwidth
- typical efficiency approx. 65 % = 1380 MB/s
- 184 pin SIMMs

Dynamic RAM technology (cont.)

Direct RAMBUS

- proprietary technology of Rambus Inc., memory architecture chosen by Intel
- new, fast DRAM architecture, 400 MHz
- operates on both rising and falling edge of clock cycle
- transfers data ovar a narrow 16-bit bus (Direct Rambus Channel)
- multiple memory banks
- use pipelining technology to send four 16-bit packets at a time (64-bit memory accesses)
- 400 MHz * 2 clocks/cycle * 16 bits / b bits = 1600 MB/s
- typical efficiency approx. 65 % = 1360 MB/s

RIMMs

- similar as DIMMs but different pin count (184 vs. 168)
- covered by an aluminium heat spreader



Registers

Small, very fast memory storage located close to the ALU
Implemented by static RAM

operates at the same speed as instruction execution

IA-32 ISA defines 8 general purpose 32-bit registers

+ special purpose registers: EIP,EFLAGS, 6 segment registers
+ 8 80 bit floating-point registers and 6 special-purpose registers
8 64-bit MMX registers, aliased to FP registers

GPR are used by the processor for operand evaluation

stores intermediate values in expression evaluation
Example:
x = G*2.41 + A/M - W*M

Optimizing compilers make efficient use of registers for expression evaluation



- write-through: data is immediately written back to memory when it is updated
- write-back: data is written to memory when a modified cache line is replaced in cache

10

Cache lines

- The unit of data transferred between RAM and cache is called a cache line
 - consists of N consecutive memory locations
- When we access a memory location, a consecutive memory block is copied to the cache
 - a cache replacement policy defines how old data in cache is replaced with new data
 - tries to keep frequently used data in the cache
 - Typical cache line sizes range from 128 bits to 512 bits
- For each memory access, the computer first checks if the cache line containing this memory location is in cache
 - if not (on a cache miss) the line is brought in
 - has to decide which old cache line to throw out LRU algorithm

11

Cache organization

- A cache mapping defines how memory locations are placed into caches
 - mapping of addresses to cache lines
- Each cache line records the memory addresses it represents
 - called a tag
 - used to find out which memory addesses are stored in a cache line
- Cache is much smaller than RAM
 - two memory blocks can be mapped to the same cache line
- Think of memory as being divided into blocks of the size of a cache line



Direct mapped caches

A memory block can be placed in exactly one cache line

- The mapping is
 - (block address) MOD (nr. of lines in cache)
- Easy to find out if a memory address is in cache or not
 - check the tag in the cache line where it is supposed to be



13

Fully associative cache

- A memory block can be placed in any cache line
- Can not calculate in which cache line a memory block should be placed
 - have to search through all cache lines to find the location containing the tag we are looking for
- Associative memory
 - search through all cache lines simultaneously for a matching tag
- Associative caches are small and expensive

Set associative cache





Compulsory cache misses

Cold start misses or first reference misses

- the first access to a block of memory always causes a cache miss when the line is brought in to the cache
- Can increase the cache line size
 - increases cache miss penalty
 - increases conflict misses, because the cache contains fewer lines

Can use prefetching

- bring in the next contigous cache line at the same time
- some processors also have a prefetch instruction, which the compiler can insert into the code
- works for contiguous memory accesses, not for random access patterns

17

Capacity cache misses

- The cache can not hold all of the memory referenced in the program
 - capacity misses occur when some cache lines are replaced because the cache is full and later need to be brought in again
- Capacity misses can be overcome by increasing the cache size
- Can also modify the data structures and algorithm to improve spatial and temporal locality
 - compiler optimization
 - high-level code optimization techniques

Conflict cache misses

- In direct mapped and set associative caches, many memory blocks can map to the same cache line
 - a cache line may have to be thrown out because some other line needs its place in the cache
 - the same line may have to be brought in immediately after
- Conflict misses can be overcome by using higher associativity
 - 4-way associative instead of 2-way
 - can also try to avoid conflict misses in the program design
- 2:1 cache rule of thumb
 - a direct mapped cache of size N has about the same miss rate as a 2-way set-associative cace of size N/2





Example of cache trashing

In the first iteration, the reference to X[0] causes a compulsory cache miss

- the cache line containing X[0] X[3] is brought in
- X[0] is placed in a register

The cache line containing Y[0] – Y[3] is brought in

- maps to the same line, replaces X[0] – X[3]
- X[0] is placed in a register

```
SIZE = 64*1024; /* 64K */
double X[SIZE], Y[SIZE];
    . . .
for (i=0; i<SIZE; i++) {
    Y[i] = X[I]+Y[i];
}</pre>
```

- X[0] and Y[0] are added and Y[0] is stored
- In the next iteration the cache line containing X[1] has to be brought in again
 - conflict cache misses in all iterations

21

Can also get cache trashing in 2-way set associative caches Three consecutive arrays of cache size X[k], Y[k] and Z[k] all map to the same set the set size is two one will always be thrown out in each iteration Can be avoided by padding the arrays insert an array of the cache line size between the arrays

 X[0], Y[0] and Z[0] map to different cache lines



Virtual memory

Decouples addresses used by the program (virtual addresses) from physical addresses

- the program uses a large contigous address space
- actual memory blocks may be located anywhere in physical memory
- some memory blocks may also be on secondary storage
- Memory is divided into pages
 - page size can be from 512 bytes to 4 MB
- Virtual addresses are translated to physical addresses using a page table



Page tables

- Stores the mapping of logical to physical addresses
- Indexed by the virtual page number
 - one entry per page in the virtual address space
- Page tables are usually large
 - stored in virtual memory
 - need two virtual-to-physical translations to find a physical address
- Use a translation lookaside buffer (TLB) as a cache for addess translations



Translation lookaside buffer

Cache memory for address translations

- tag field holds a part of the virtual address
- data field holds the physical page frame number
- also status bits: valid, use, dirty
- Implemented by an associative cache memory
- TLB is limited in size
 - virtual addresses not in the TLB cause a TLB miss
- Repeated TLB misses cause very bad performance
 - same as for repeated cache misses
- Good cache behaviour usually implies good TLB behaviour